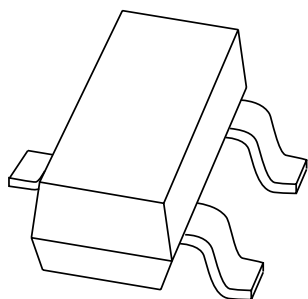


# DATA SHEET



## **PDTTC114TT** NPN resistor-equipped transistor

Objective specification  
File under Discrete Semiconductors, SC04

1997 Jul 14

# NPN resistor-equipped transistor

# PDTC114TT

### FEATURES

- Built-in bias resistor R1 (typ. 10 kΩ)
- Simplification of circuit design
- Reduces number of components and board space.

### APPLICATIONS

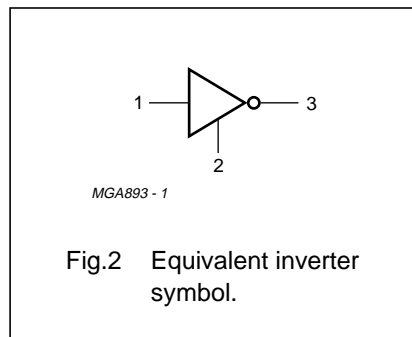
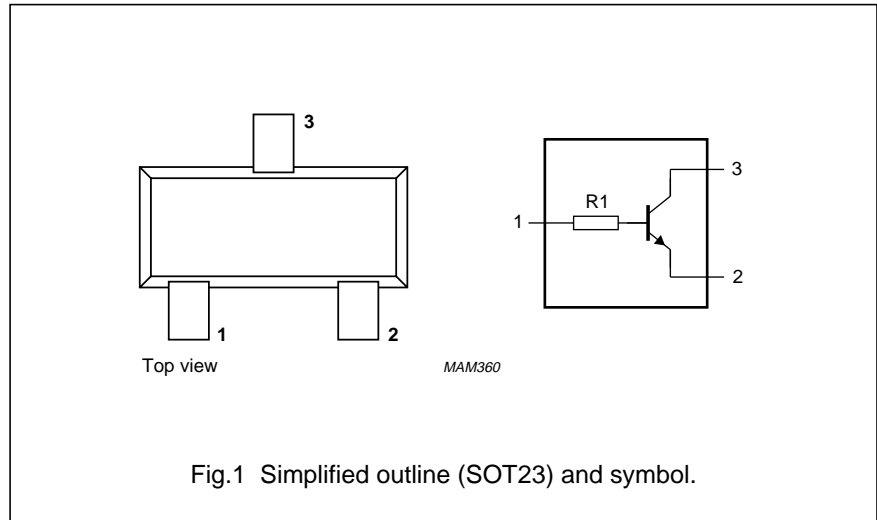
- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configurations without use of an external resistor.

### DESCRIPTION

NPN resistor-equipped transistor in a SOT23 plastic package.  
 PNP complement: PDA114TT.

### PINNING

| PIN | DESCRIPTION      |
|-----|------------------|
| 1   | base/input       |
| 2   | emitter/ground   |
| 3   | collector/output |



### MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| PDTC114TT   | p12          |

### QUICK REFERENCE DATA

| SYMBOL    | PARAMETER                 | CONDITIONS                               | MIN. | TYP. | MAX. | UNIT |
|-----------|---------------------------|--|------|------|------|------|
| $V_{CE0}$ | collector-emitter voltage | open base                                | –    | –    | 50   | V    |
| $I_O$     | output current (DC)       |  | –    | –    | 100  | mA   |
| $I_{CM}$  | peak collector current    |  | –    | –    | 100  | mA   |
| $P_{tot}$ | total power dissipation   | $T_{amb} \leq 25\text{ }^\circ\text{C}$  | –    | –    | 250  | mW   |
| $h_{FE}$  | DC current gain           | $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$ | 100  | –    | 600  |      |
| R1        | input resistor            |  | 7    | 10   | 13   | kΩ   |

## NPN resistor-equipped transistor

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL    | PARAMETER                     | CONDITIONS                           | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--------------------------------------|------|------|------|
| $V_{CBO}$ | collector-base voltage        | open emitter                         | –    | 50   | V    |
| $V_{CEO}$ | collector-emitter voltage     | open base                            | –    | 50   | V    |
| $V_{EBO}$ | emitter-base voltage          | open collector                       | –    | 5    | V    |
| $I_O$     | output current (DC)           |                                      | –    | 100  | mA   |
| $I_{CM}$  | peak collector current        |                                      | –    | 100  | mA   |
| $P_{tot}$ | total power dissipation       | $T_{amb} \leq 25\text{ °C}$ ; note 1 | –    | 250  | mW   |
| $T_{stg}$ | storage temperature           |                                      | –65  | +150 | °C   |
| $T_j$     | junction temperature          |                                      | –    | 150  | °C   |
| $T_{amb}$ | operating ambient temperature |                                      | –65  | +150 | °C   |

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1     | 500   | K/W  |

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS  | MIN. | TYP. | MAX. | UNIT          |
|-------------|--------------------------------------|---|------|------|------|---------------|
| $I_{CBO}$   | collector cut-off current            | $I_E = 0$ ; $V_{CB} = 50\text{ V}$                            | –    | –    | 100  | nA            |
| $I_{CEO}$   | collector cut-off current            | $I_B = 0$ ; $V_{CE} = 30\text{ V}$                            | –    | –    | 1    | $\mu\text{A}$ |
|             |                                      | $I_B = 0$ ; $V_{CE} = 30\text{ V}$ ; $T_j = 150\text{ °C}$    | –    | –    | 50   | $\mu\text{A}$ |
| $I_{EBO}$   | emitter cut-off current              | $I_C = 0$ ; $V_{EB} = 5\text{ V}$                             | –    | –    | 100  | nA            |
| $h_{FE}$    | DC current gain                      | $I_C = 1\text{ mA}$ ; $V_{CE} = 5\text{ V}$                   | 100  | –    | 600  |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = 10\text{ mA}$ ; $I_B = 0.5\text{ mA}$                  | –    | –    | 300  | mV            |
| R1          | input resistor                       |   | 7    | 10   | 13   | k $\Omega$    |
| $C_c$       | collector capacitance                | $I_E = i_e = 0$ ; $V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$ | –    | –    | 3.5  | pF            |

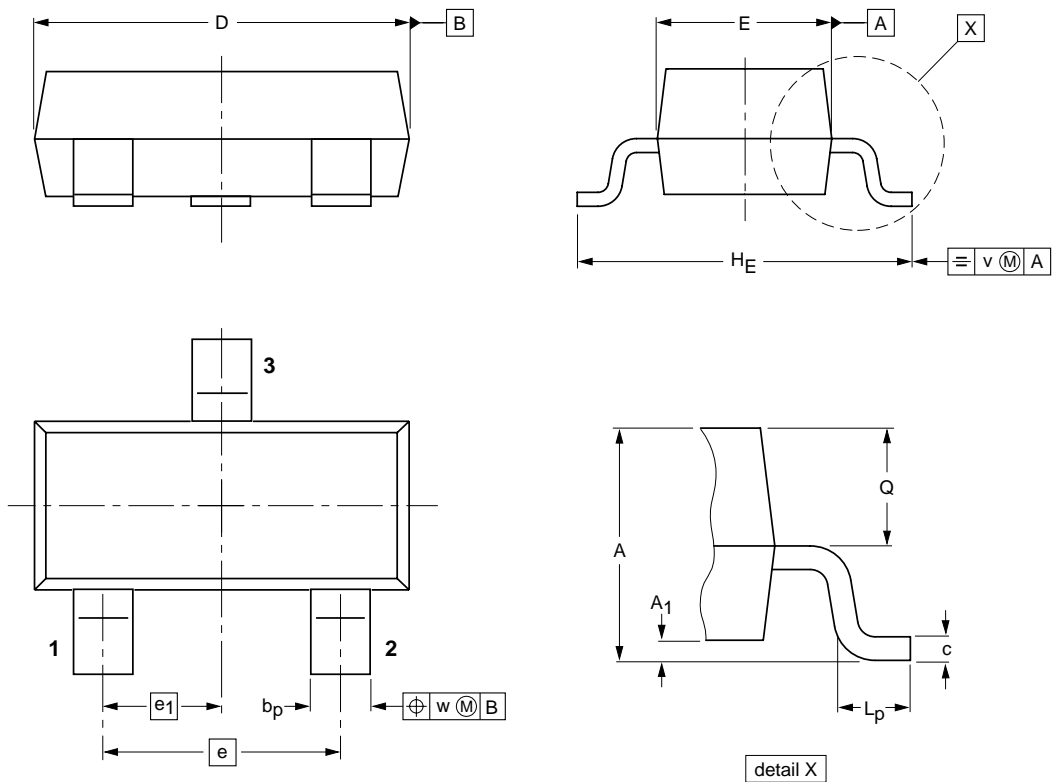
NPN resistor-equipped transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub><br>max. | b <sub>p</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | Q            | v   | w   |
|------|------------|------------------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm   | 1.1<br>0.9 | 0.1                    | 0.48<br>0.38   | 0.15<br>0.09 | 3.0<br>2.8 | 1.4<br>1.2 | 1.9 | 0.95           | 2.5<br>2.1     | 0.45<br>0.15   | 0.55<br>0.45 | 0.2 | 0.1 |

| OUTLINE<br>VERSION | REFERENCES |       |      |  | EUROPEAN<br>PROJECTION | ISSUE DATE |
|--------------------|------------|-------|------|--|------------------------|------------|
|                    | IEC        | JEDEC | EIAJ |  |                        |            |
| SOT23              |            |       |      |  |                        | 97-02-28   |

## NPN resistor-equipped transistor

PDTC114TT

**DEFINITIONS**

| <b>Data Sheet Status</b>  |   |
|---|---|
| Objective specification   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification   | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification   | This data sheet contains final product specifications.                                |
| <b>Limiting values</b>  |   |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |   |
| <b>Application information</b>  |   |
| Where application information is given, it is advisory and does not form part of the specification.   |   |

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NPN resistor-equipped transistor

PDTC114TT

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**NOTES**

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NPN resistor-equipped transistor

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**NOTES**

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